

BYC40W-1200P

Hyperfast power diode Rev.01 - 14 November 2018

Product data sheet

1. General description

EEPP[™]- Efficiency Enhanced Pt Planar rectifier in a TO247-2L plastic package.

2. Features and benefits

- Fast switching
- · Reduces switching losses with improved lower reverse recovery charge
- Soft recovery characteristics
- Low thermal resistance
- Low leakage current
- Planar termination structure
- High operating temperature capability ($T_{j (max)} = 175^{\circ}C$)
- Higher I_{FSM} capability

3. Applications

- Switched-Mode Power Supplies
- Power factor correction diode
- Uninterrupted Power Supply

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			1200			V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 96 °C; Fig. 1; Fig. 2; Fig. 3		40		A	
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 96 °C; square-wave pulse		80		A	
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	300 330			A	
		$t_{\rm p}$ = 8.3 ms; $T_{j(\text{init})}$ = 25 °C; sine-wave pulse;			А		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics	·					
V _F	forward voltage	I _F = 40 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.8	3.3	V
		I _F = 40 A; T _j = 150 °C; <u>Fig. 6</u>		-	2.2	-	V
Dynamic	characteristics	·					
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _j = 25 °C; <u>Fig. 7</u>		-	52	-	ns
Avalanch	ne energy						
E _{AS}	non-repetitive avalanche energy	T _{j(init)} = 25 °C		30	-	-	mJ

5. Pinning information

Table 2. P	inning infor	mation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		K — A 001aaa020
2	А	anode	μΟϥ	001888020
mb	mb	mounting base; connected to cathod	6 1 1 1 1 1 1 1 1 1 1	

6. Ordering information

Table 3. Ordering information								
Type number	Package	Orderable part number	Packing	Small packing	Package	Package		
	name		method	quantity	version	issue date		
BYC40W-1200P	TO247-2L	BYC40W-1200PQ	Tube	30	TO247A-2L	23-Jun-2017		

7. Marking

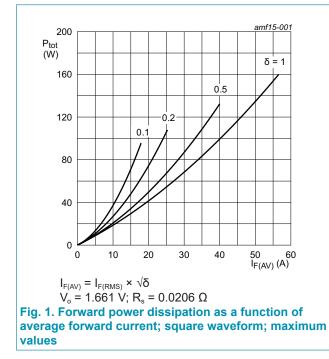
Table 4. Marking codes					
Type number	Marking codes				
BYC40W-1200P	BYC40W-1200P				

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		1200	V
V _{RWM}	crest working reverse voltage		1200	V
V _R	reverse voltage	DC	1200	V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 96 °C; Fig. 1; Fig. 2; Fig. 3	40	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 96 °C; square-wave pulse	80	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	300	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	330	A
T _{stg}	storage temperature		-65 to 175	°C
Tj	junction temperature		175	°C



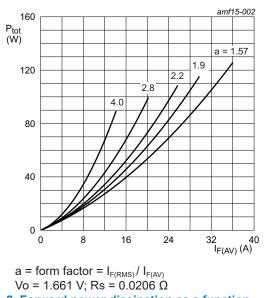
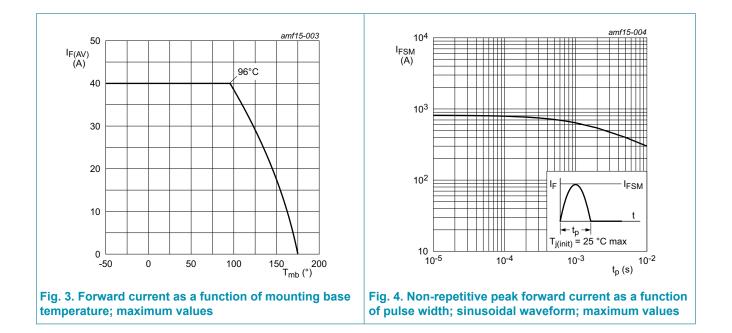


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

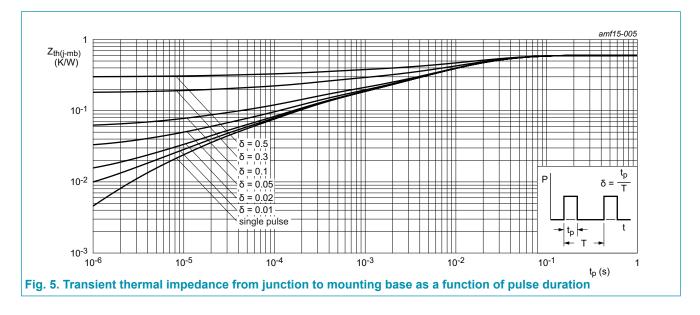
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9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	0.6	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W



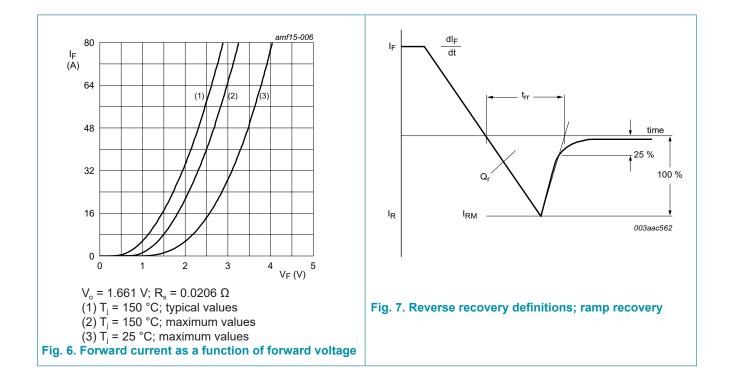
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10. Characteristics

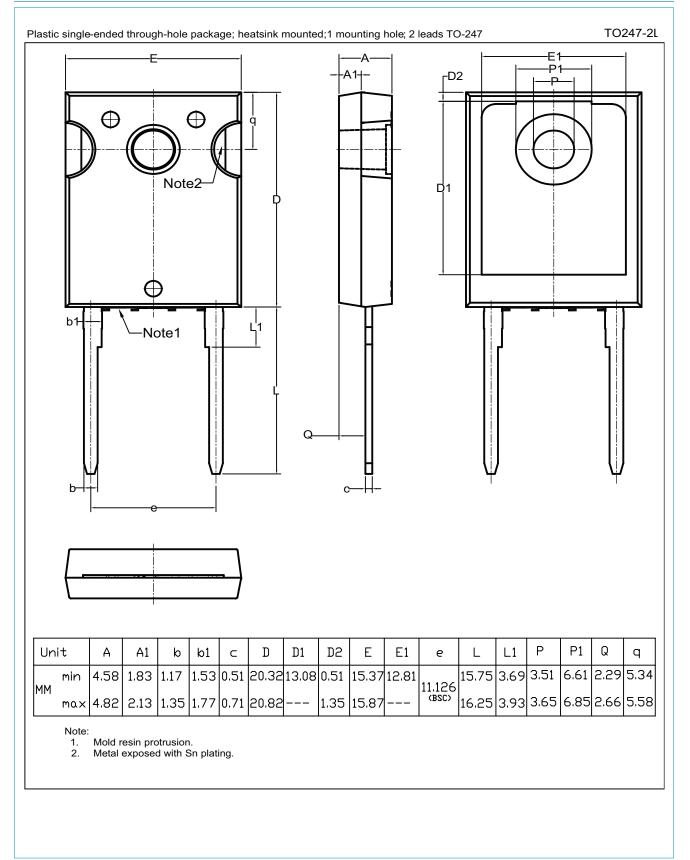
Symbol	naracteristics Parameter	Conditions	Min	Тур	Max	Unit
	aracteristics	Conditions	IVIIII	קעי	INIAA	Unit
				0.0	0.0	
V _F	forward current	$I_{F} = 40 \text{ A}; T_{j} = 25 \text{ °C}; Fig. 6$	-	2.8	3.3	V
		I _F = 40 A; T _j = 150 °C; <u>Fig. 6</u>	-	2.2	-	V
I _R	reverse current	V _R = 1200 V; T _j = 25 °C	-	-	250	μA
		V _R = 1200 V; T _j = 150 °C	-	-	2	mA
Dynamic	characteristics	· · · · · ·	I			_
Q _r	reverse charge	$I_F = 40 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	863	-	nC
		$I_F = 40 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	2314	-	nC
		I _F = 40 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _j = 150 °C; <u>Fig. 7</u>	-	2637	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	52	-	ns
		$I_F = 40 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_J = 25 \text{ °C}; Fig. 7$	-	91	-	ns
		$I_F = 40 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	172	-	ns
		$I_F = 40 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	186	-	ns
I _{RM}	peak reverse recovery current	$I_F = 40 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	19	-	A
		I _F = 40 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _i = 125 °C; <u>Fig. 7</u>	-	27	-	A
		I _F = 40 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _j = 150 °C; <u>Fig. 7</u>	-	28.4	-	А
Avalanch	e energy	· · · · · ·				
E _{AS}	non-repetitive avalanche energy	T _{j(init)} = 25 °C	30	-	-	mJ

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11. Package outline



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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